# N-Channel 100-V (D-S) MOSFET

### **Key Features:**

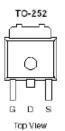
- Low r<sub>DS(on)</sub> trench technology
- Low thermal impedance
- Fast switching speed

## **Typical Applications:**

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY			
VDS (V)	$r_{DS(on)}(m\Omega)$	Id(A)	
100	18 @ V <sub>GS</sub> = 10V	43	
	24 @ V <sub>GS</sub> = 5.5V	37	





ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage		V <sub>DS</sub>	100	V		
Gate-Source Voltage		V <sub>GS</sub>	±20	v		
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> =25 °C		43	۸		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	160	A		
Continuous Source Current (Diode Conduction) <sup>a</sup>			55	Α		
Power Dissipation <sup>a</sup>	T <sub>C</sub> =25 °C	C P <sub>D</sub>	50	W		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient <sup>a</sup>	R <sub>θJA</sub>	40	℃/W		
Maximum Junction-to-Case	R <sub>eJC</sub>	3	C/ W		

#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

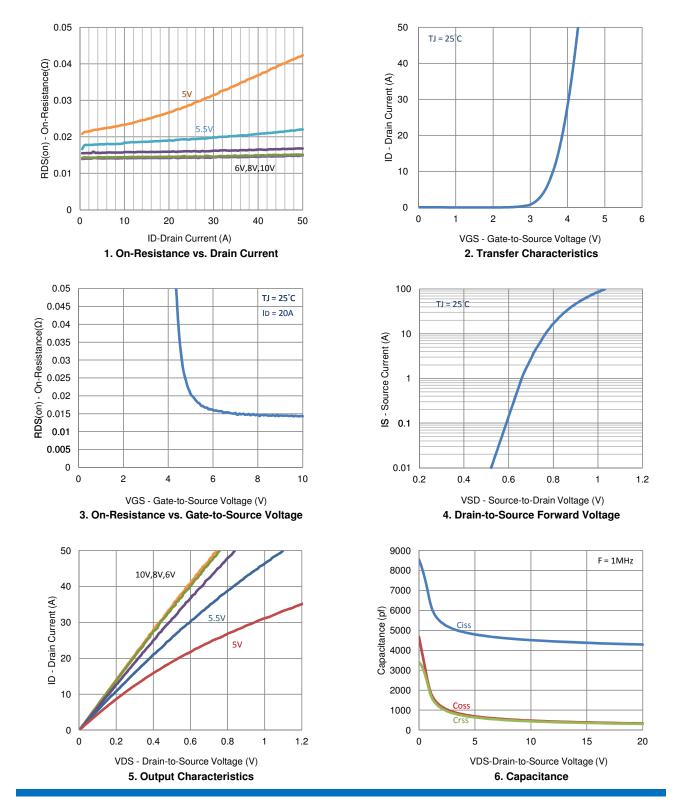
## **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
		Static		•			
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			±100	nA	
Zava Cata Valtaga Drain Current		$V_{\text{DS}} = 80 \text{ V},  V_{\text{GS}} = 0 \text{ V}$			1	uА	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 80 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55 ^{\circ}\text{C}$			25	uA	
On-State Drain Current	I <sub>D(on)</sub>	$V_{DS} = 5 V, V_{GS} = 10 V$	50			А	
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$			18	mΩ	
	r <sub>DS(on)</sub>	$V_{GS} = 5.5 \text{ V}, \text{ I}_{D} = 16 \text{ A}$			24		
Forward Transconductance	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		22		S	
Diode Forward Voltage	V <sub>SD</sub>	$I_{\rm S}$ = 27.5 A, $V_{\rm GS}$ = 0 V		0.85		V	
		Dynamic					
Total Gate Charge	Qg	$V_{DS} = 50 \text{ V}, \text{ V}_{GS} = 5.5 \text{ V},$		60		nC	
Gate-Source Charge	Q <sub>gs</sub>	$v_{\rm DS} = 50$ V, $v_{\rm GS} = 5.5$ V, $I_{\rm D} = 20$ A		15			
Gate-Drain Charge	Q <sub>gd</sub>	10 - 20 7		36			
Turn-On Delay Time	t <sub>d(on)</sub>			19			
Rise Time	tr	$V_{DS} = 50 \text{ V}, \text{ R}_{L} = 2.5 \Omega,$ $I_{D} = 20 \text{ A},$		42		20	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{\text{GEN}} = 20 \text{ A},$ $V_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{GEN}} = 6 \Omega$		129		ns	
Fall Time	t <sub>f</sub>	$\mathbf{V}_{\text{GEN}} = 10 \mathbf{V}, 10_{\text{GEN}} = 0 12$		46			
Input Capacitance	C <sub>iss</sub>			4376			
Output Capacitance	C <sub>oss</sub>	$V_{\text{DS}}$ = 15 V, $V_{\text{GS}}$ = 0 V, f = 1 MHz		389		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	]		358			

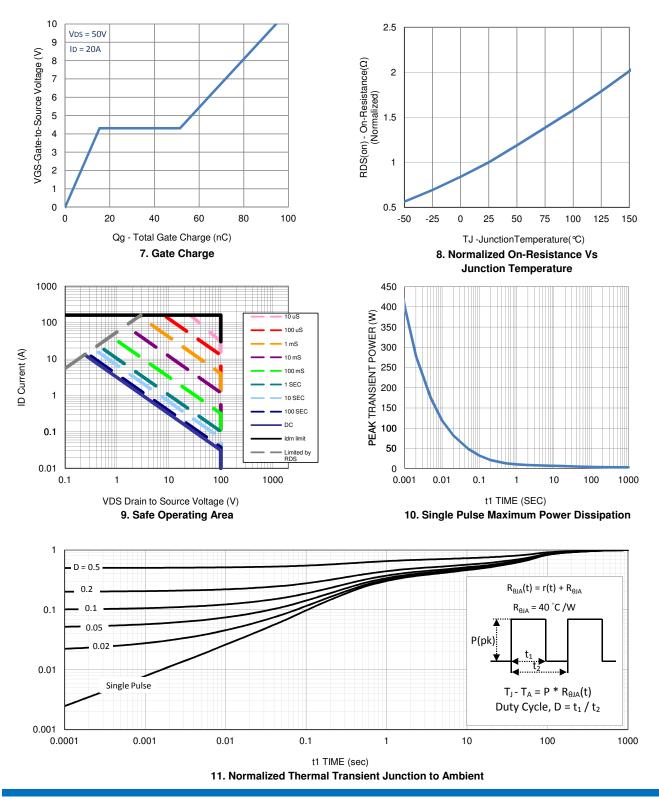
Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

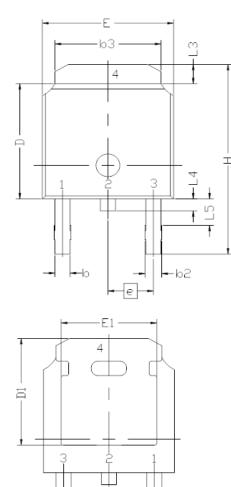
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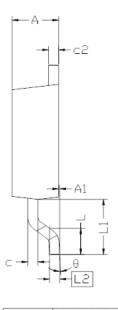
### **Typical Electrical Characteristics**



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SINGLE ROWNEW



DIMENSIONAL REQM				
SYMBOL	MIN	NDM	MAX	
E	6.40	6.60	6.731	
L	1.40	1.52	1.77	
L1	2	.743 R	ÉF	
L2	0.	.508 BS		
L3	0.89		1.27	
L4	0.64		1.01	
L5				
D	6.00	6.10	6,223	
Н	9.40	10.00	10.40	
b	0.64	0.76	0.88	
b2	0.77	0.84	1.14	
b3	5.21	5.34	5.46	
e		286 BS		
A	2.20	2.30	2.38	
A1	0		0.127	
C	0.45	0.50	0.60	
c2	0.45	0.50	0.58	
D1	5.30			
E1	4.40			
θ	0*		10°	

#### Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.

5

**Package Information**